

/ Descriptions

WR0459I ММ Ё QSQ Æ М ы s ll 1 Silicon NPN transistor in a TO-126F Plastic Package.

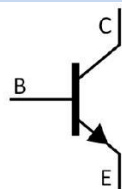
/ Features

Љ 5VD : 48 Ў ´
Complementary pair with 2SA715.

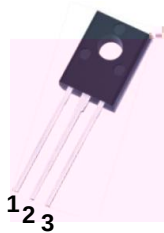
/ Applications

Љ H Ё I ' ђ z
Low frequency power amplifier.

/ Equivalent Circuit



/ Pinning



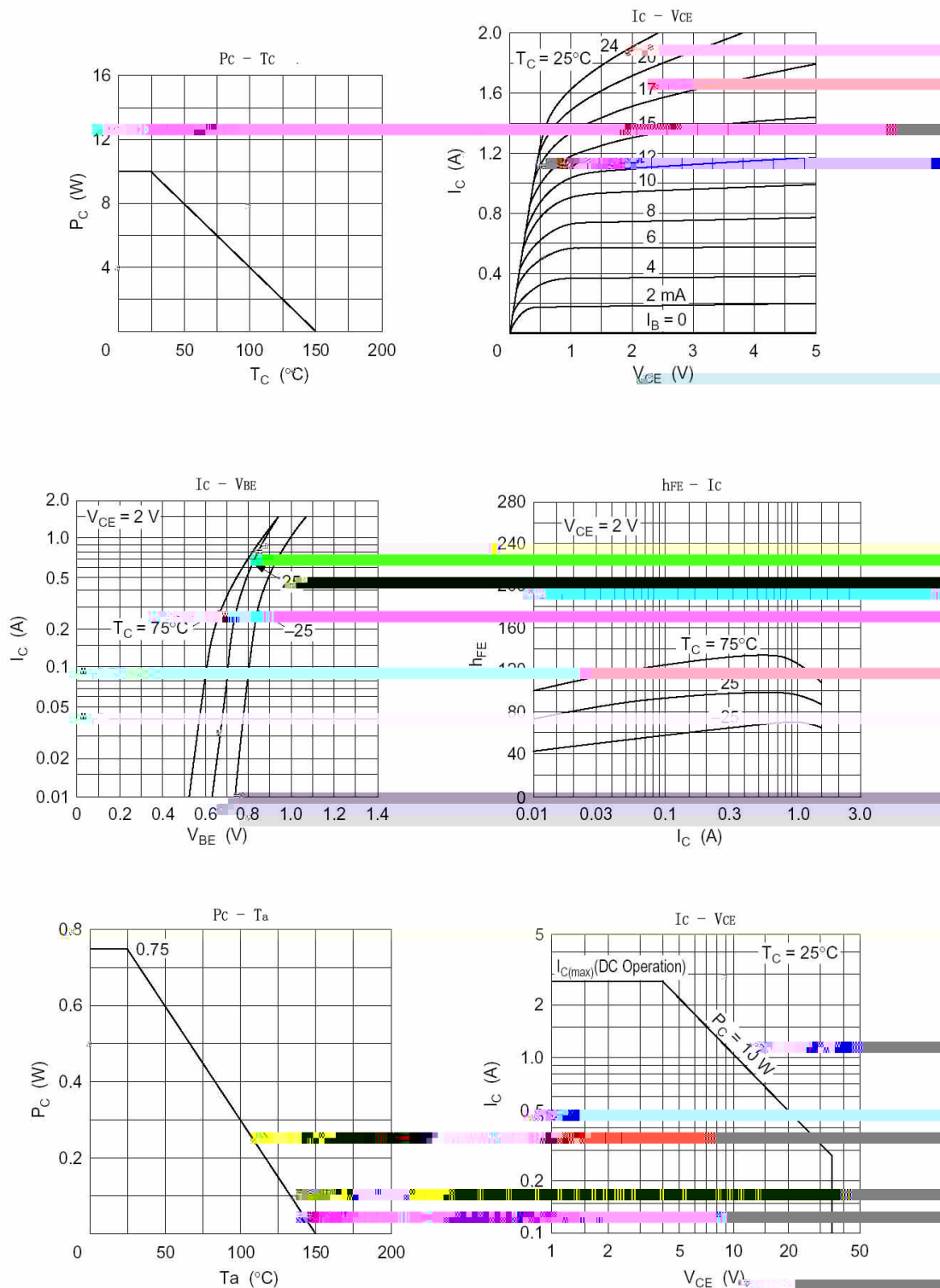
PIN1 χ Emitter PIN 2 χ Collector PIN 3 χ Base

/ h_{FE} Classifications & Marking

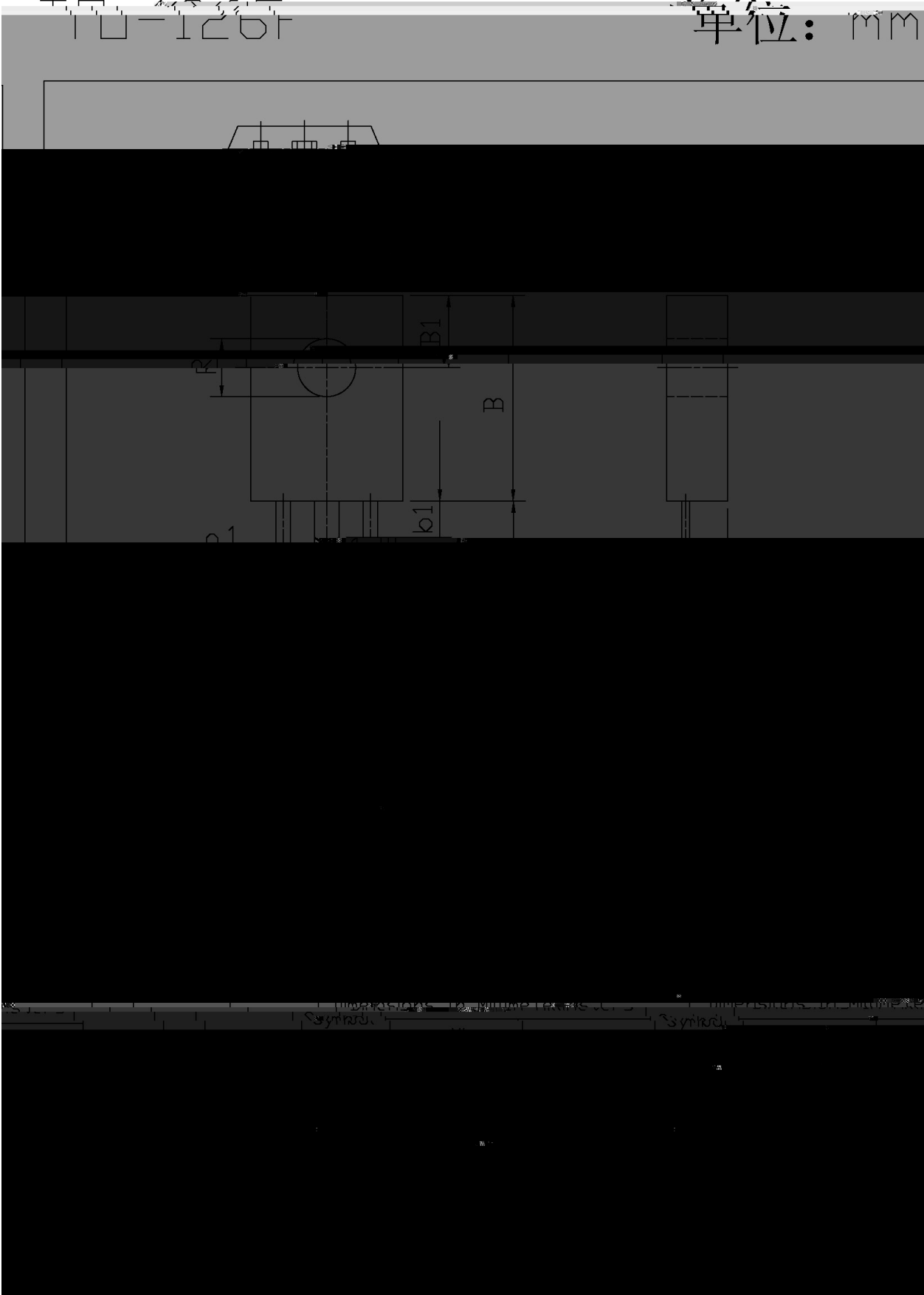
h _{FE} Classifications Symbol	B	C	D
h _{FE} Range	60 120	100 200	160 320

Parameter	Symbol	Rating	Unit
Collector to Base Voltage	V_{CBO}	35	V

/ Electrical Characteristic Curve



/ Package Dimensions





() / Temperature Profile for Dip Soldering(Pb-Free)



б " X

1. 1. Preheating: 25~150 °C, Time: 60~90sec;
2. 2. Peak Temp.: 255 °C, Duration: 5~10sec;
3. 3. Cooling Speed: 2~10 °C/sec.

Note:

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2. Peak Temp.: 255 °C, Duration: 5~10sec.
3. Cooling Speed: 2~10 °C/sec.

/ Resistance to Soldering Heat Test Conditions

□ °C 270 ± 5 °C °C 10 ± 1 sec. Temp.: 270 ± 5 Time: 10 ± 1 sec

/ Packaging SPEC.

“Q” γ t / BULK

Package Type	Units					Dimension (unit mm ³)		
	Units/Tube	Tubes/Inner Box	Units/Inner Box	Inner Boxes/Outer Box	Units/Outer Box	Tube	Inner Box	Outer Box
TO-126/F	500	6	3,000	5	15,000	135×190	237×172×102	560×245×195

“γ” γ t / TUBE

Package Type	Units					Dimension (unit mm ³)		
	Units/Tube	Tubes/Inner Box	Units/Inner Box	Inner Boxes/Outer Box	Units/Outer Box	Tube	Inner Box	Outer Box
TO-126/F	65	26	1,690	5	8,450	532×31×5.6	555×164×50	575×290×180